

Product Summary

Part Number	V _{GS(off)} (V)	V _{(BR)GSS} Min (V)	I _{DSS} Min (mA)	r _{D(on)} Max (Ω)	I _{D(off)} Typ (pA)	t _{ON} Typ (ns)
2N4856A	-4 to -10	-40	50	25	5	4
2N4857A	-2 to -6	-40	20	40	5	4
2N4858A	-0.8 to -4	-40	8	60	5	4

Features

- Low On-Resistance: 2N4856A <25 Ω
- Fast Switching—t_{ON}: 4 ns
- High Off-Isolation—I_{D(off)}: 5 pA
- Low Capacitance: 3 pF
- Low Insertion Loss

Benefits

- Low Error Voltage
- High-Speed Analog Circuit Performance
- Negligible “Off-Error,” Excellent Accuracy
- Good Frequency Response
- Eliminates Additional Buffering

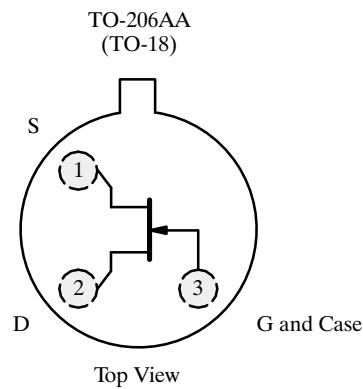
Applications

- Analog Switches
- Choppers
- Sample-and-Hold
- Normally “On” Switches
- Current Limiters

Description

The 2N4856A/4857A/4858A all-purpose JFET analog switches offer low on-resistance, low capacitance, good isolation, and fast switching.

Hermetically-sealed TO-206AA (TO-18) packaging allows full military processing (see Military Information). For similar products in TO-226AA (TO-92) and SOT-23 packages, see the J/SST111 series data sheet. For similar duals, see the 2N5564/5565/5566 data sheet.



Absolute Maximum Ratings

Gate-Drain, Gate-Source Voltage : (2N4856A-58A)	-40 V
Gate Current	50 mA
Lead Temperature (1/16" from case for 10 seconds)	300 °C
Storage Temperature	-65 to 200°C

Operating Junction Temperature	-55 to 200°C
Power Dissipation ^a	1.8 W

Notes

a. Derate 10 mW/°C for T_C > 25°C

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Specifications^a

Parameter	Symbol	Test Conditions	Typ ^b	Limits						Unit	
				2N4856A		2N4857A		2N4858A			
				Min	Max	Min	Max	Min	Max		
Static											
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA, V _{DS} = 0 V	-55	-40		-40		-40		V	
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 15 V, I _D = 0.5 nA		-4	-10	-2	-6	-0.8	-4		
Saturation Drain Current ^c	I _{DSS}	V _{DS} = 15 V, V _{GS} = 0 V		50		20	100	8	80	mA	
Gate Reverse Current	I _{GSS}	V _{GS} = -20 V, V _{DS} = 0 V	-5		-250		-250		-250	pA	
			T _A = 150°C	-13		-500		-500		nA	
Gate Operating Current ^d	I _G	V _{DG} = 15 V, I _D = 10 mA	-5							pA	
Drain Cutoff Current	I _{D(off)}	V _{DS} = 15 V, V _{GS} = -10 V	5		250		250		250		
			T _A = 150°C	13		500		500		nA	
Drain-Source On-Voltage	V _{DS(on)}	V _{GS} = 0 V	I _D = 5 mA	0.25					0.5	V	
			I _D = 10 mA	0.35				0.5			
			I _D = 20 mA	0.5		0.75					
Drain-Source On-Resistance ^d	r _{DS(on)}	V _{GS} = 0 V, I _D = 1 mA			25		40		60	Ω	
Gate-Source Forward Voltage ^d	V _{GS(F)}	I _G = 1 mA, V _{DS} = 0 V	0.7							V	
Dynamic											
Common-Source Forward Transconductance ^d	g _{fs}	V _{DS} = 20 V, I _D = 1 mA f = 1 kHz	6							mS	
Common-Source Output Conductance ^d	g _{os}		25							μS	
Drain-Source On-Resistance	r _{ds(on)}	V _{GS} = 0 V, I _D = 0 mA f = 1 kHz			25		40		60	Ω	
Common-Source Input Capacitance	C _{iss}	V _{DS} = 0 V, V _{GS} = -10 V f = 1 MHz	7		10		10		10	pF	
Common-Source Reverse Transfer Capacitance	C _{rss}		3		4		3.5		3.5		
Equivalent Input Noise Voltage ^d	ē _n	V _{DS} = 10 V, I _D = 10 mA f = 1 kHz	3							nV/ √Hz	
Switching											
Turn-On Time	t _{d(on)}	V _{DD} = 10 V, V _{GSH} = 0 V See Switching Circuit	2		5		6		8	ns	
	t _r		2		3		4		8		
Turn-Off Time	t _{OFF}		12		20		40		80		

Notes

- a. T_A = 25°C unless otherwise noted.
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
c. Pulse test: PW ≤ 100 μs duty cycle ≤ 10%.
d. This parameter not registered with JEDEC.

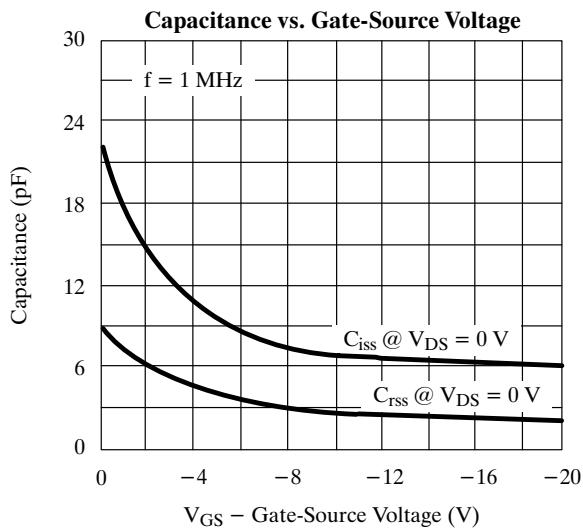
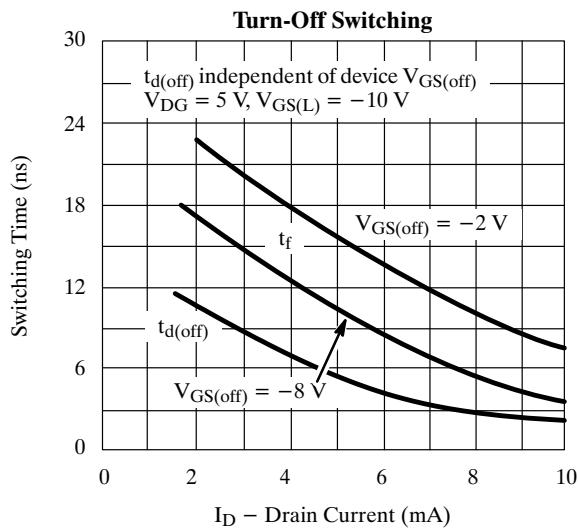
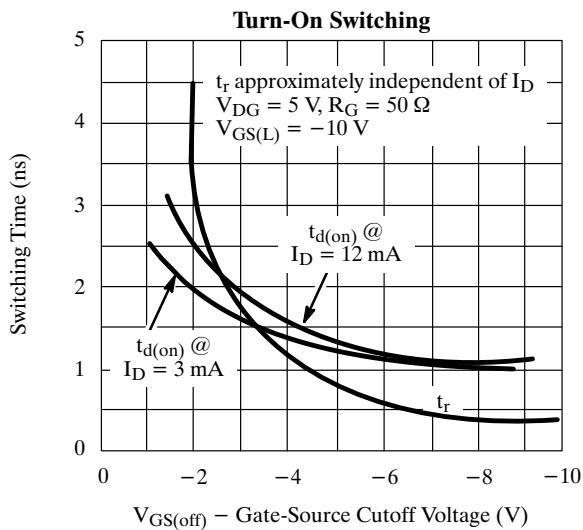
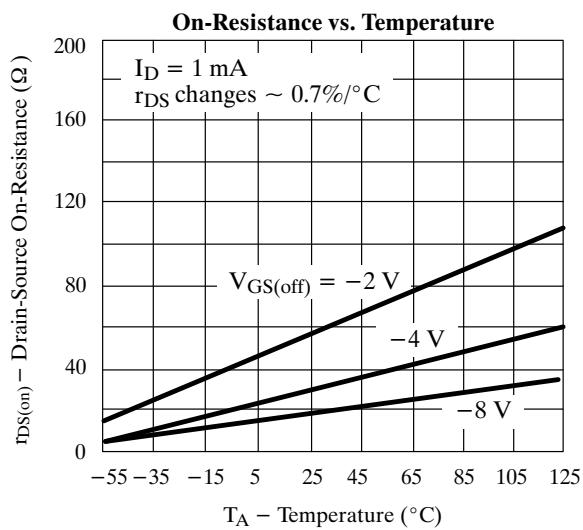
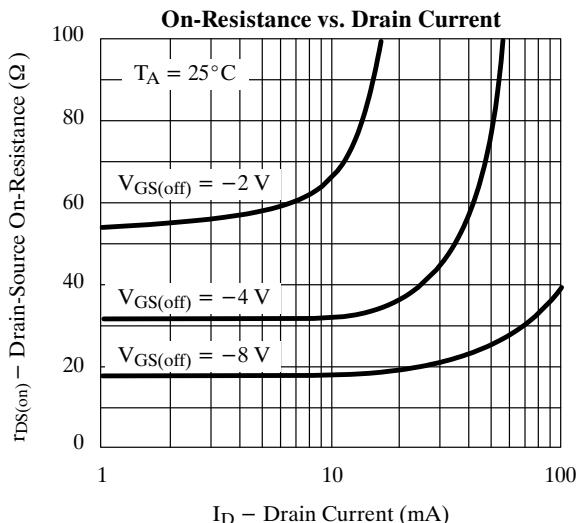
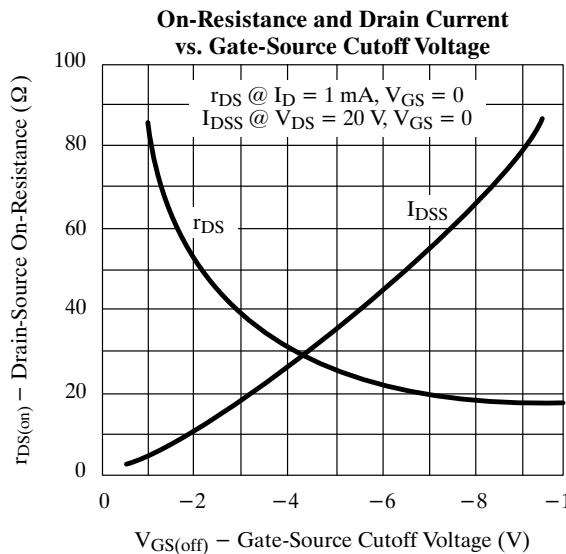
NCB

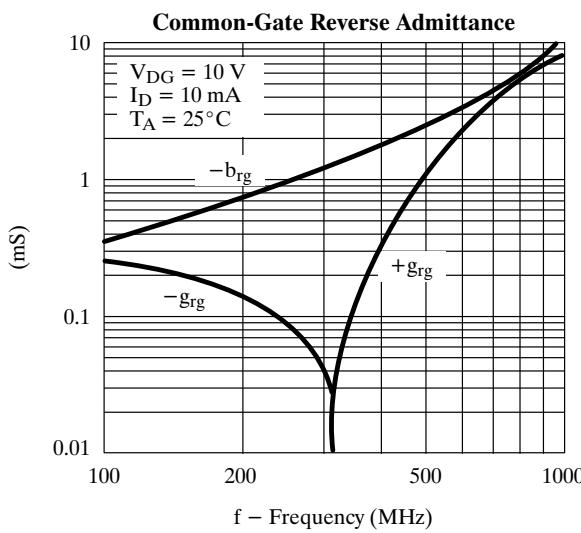
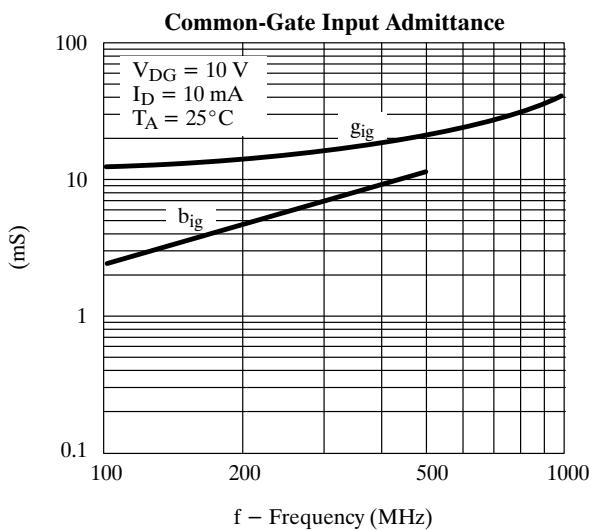
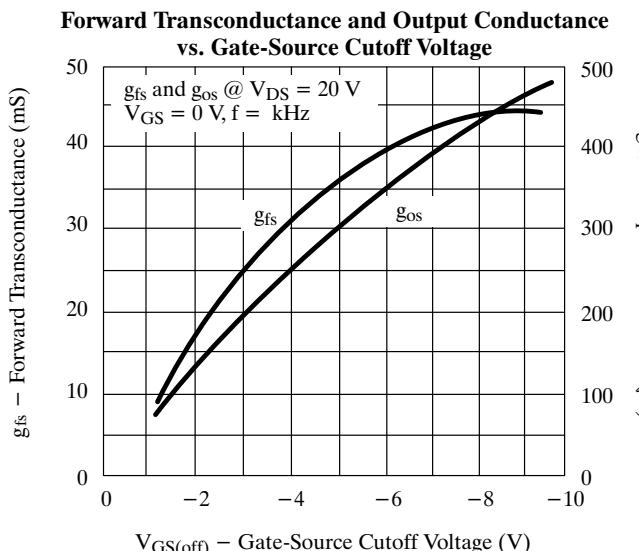
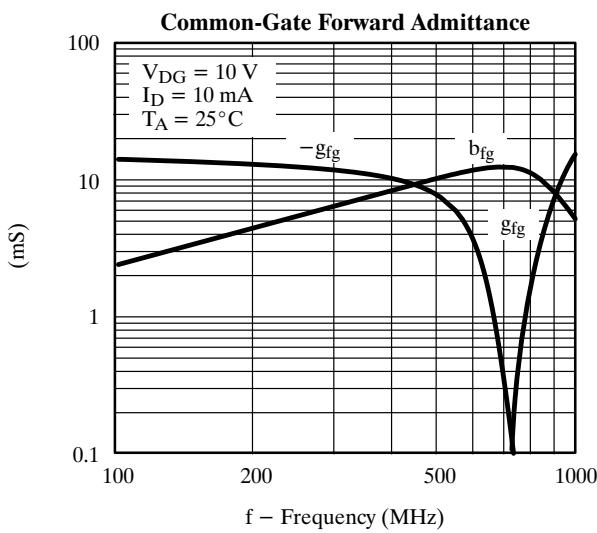
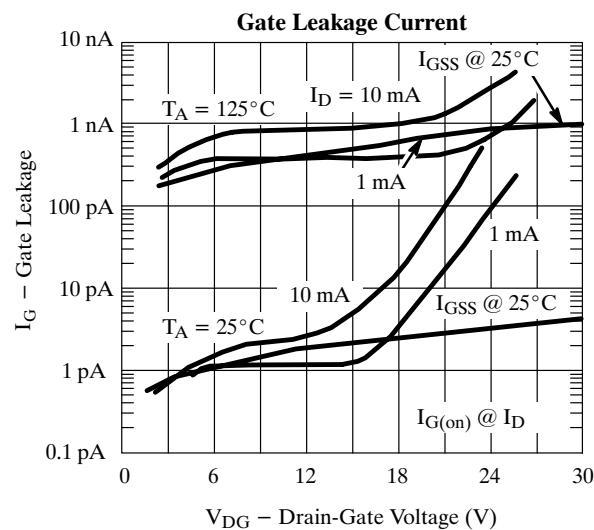
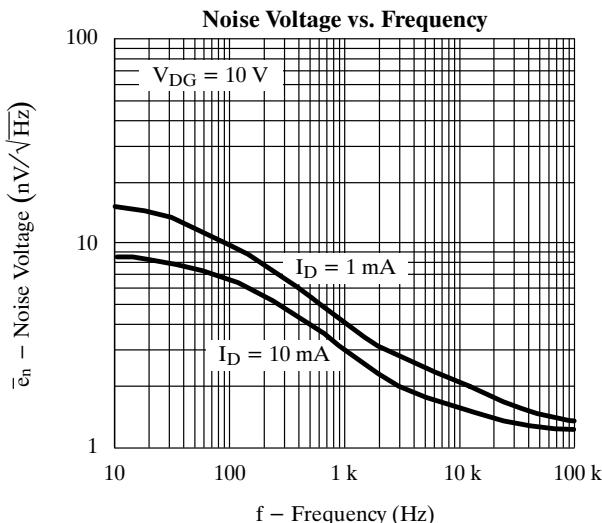
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Typical Characteristics



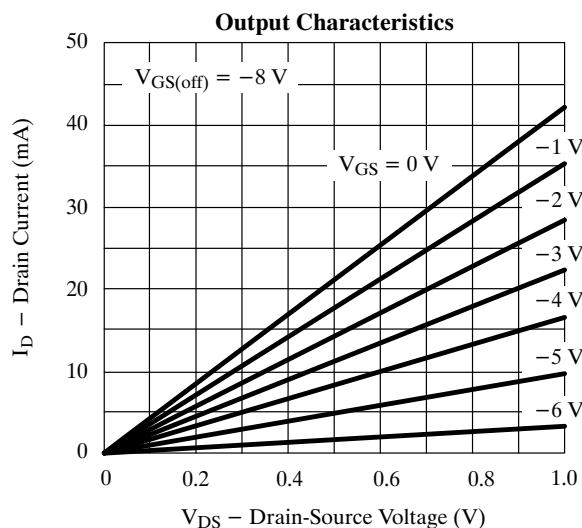
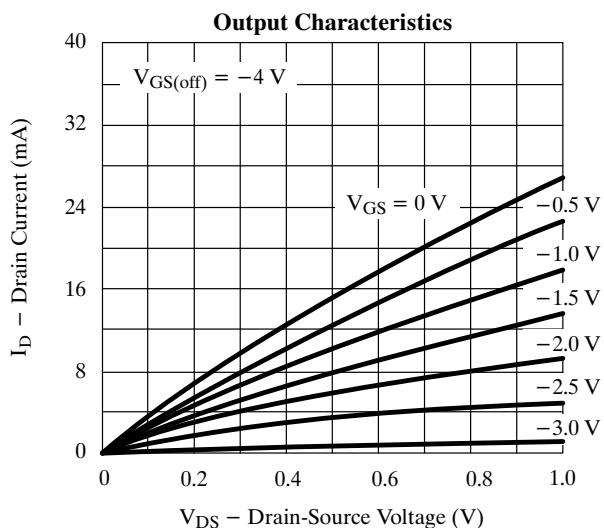
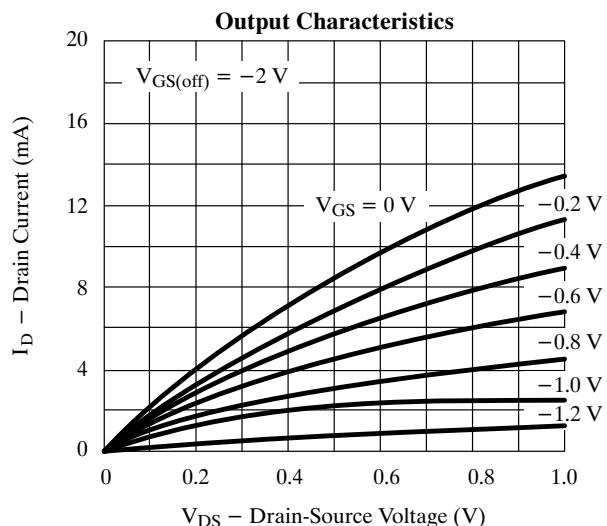
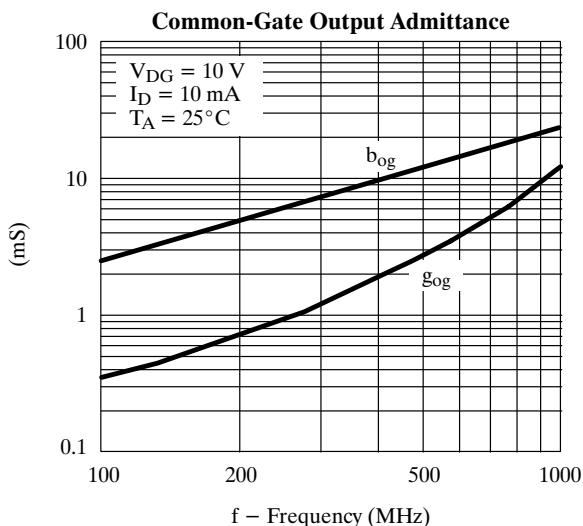
2N4856A/4857A/4858A**Typical Characteristics (Cont'd)**

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Typical Characteristics (Cont'd)



Switching Time Test Circuit

	2N4856A	2N4857A	2N4858A
$V_{GS(L)}$	-10 V	-6 V	-4 V
R_L^*	464 Ω	953 Ω	1910 Ω
$I_{D(on)}$	20 mA	10 mA	5 mA

*Non-inductive

Input Pulse

Rise Time < 1 ns
Fall Time < 1 ns
Pulse Width 100 ns
PRF 1 MHz

Sampling Scope

Rise Time 0.4 ns
Input Resistance 10 M Ω
Input Capacitance 1.5 pF

